

**800V N- CHANNEL ENHANCEMENT MODE MOSFET**
**MAIN CHARACTERISTICS**

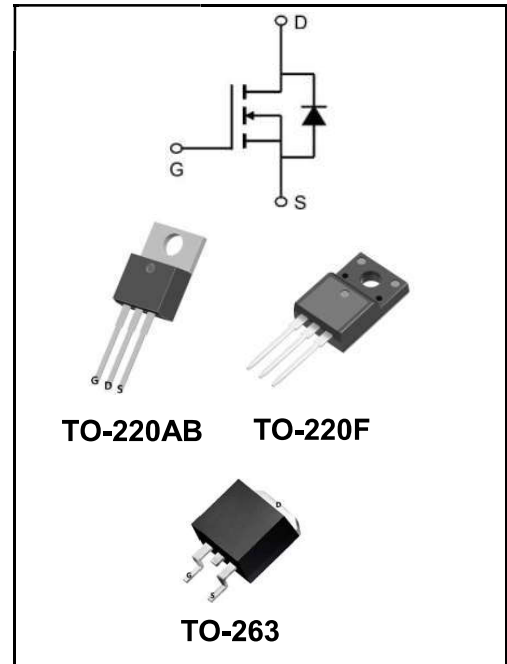
<b>I<sub>D</sub></b>	6A
<b>V<sub>DSS</sub></b>	800V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	< 1.5Ω

**Features**

- ◆High EAS(on) & FOM
- ◆Extremely low switching loss
- ◆Excellent stability and uniformity or Invertors

**Application**

- ◆Consumer electronic power supply Motor control
- ◆Synchronous-rectification Isolated DC
- ◆Synchronous-rectification applications


**Product Specification Classification**

Part Number	Package	Marking	Pack
YFW6N80AT	TO-220AB	YFW 6N80AT XXXXX	1000PCS/Box
YFW6N80AF	TO-220F	YFW 6N80AF XXXXX	1000PCS/Box
YFW6N80AS	TO-263	YFW 6N80AS XXXXX	800PCS/Reel

**Maximum Ratings at T<sub>c</sub>=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	800	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±30	<b>V</b>
Drain Current, V <sub>GS</sub> @ 10V <sup>3</sup> T <sub>C</sub> =25°C	<b>I<sub>D</sub></b>	6	<b>A</b>
Pulsed Drain Current <sup>1</sup>	<b>I<sub>DM</sub></b>	24	<b>A</b>
Total Power Dissipation T <sub>C</sub> =25 °C	<b>P<sub>D</sub></b>	34.7	<b>W</b>
Total Power Dissipation T <sub>A</sub> =25 °C		1.92	
Single Pulse Avalanche Energy <sup>4</sup>	<b>E<sub>AS</sub></b>	18	<b>mJ</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to 150	<b>°C</b>
Operating Junction Temperature Range	<b>T<sub>J</sub></b>	-55 to 150	<b>°C</b>
Maximum Thermal Resistance, Junction-case	<b>R<sub>θJC</sub></b>	3.6	<b>°C/W</b>
Maximum Thermal Resistance, Junction-ambient	<b>R<sub>θJA</sub></b>	65	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	800	-	-	V
Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=3A$	$R_{DS(ON)}$	-	-	1.5	$\Omega$
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	2.5	-	4.5	V
Forward Transconductance	$V_{DS}=20V, I_D=3A$	$g_{fs}$	-	8	-	S
Drain-source leakage current	$V_{DS}=640V, V_{GS}=0V$	$I_{DSS}$	-	-	100	$\mu A$
Gate Source Leakage	$V_{GS}=\pm 30V, V_{DS}=0V$	$I_{GSS}$	-	-	$\pm 1$	nA
Total Gate Charge	$I_D=7A$ $V_{DS}=640V$ $V_{GS}=10V$	$Q_g$	-	41	65.6	nC
Gate-Source Charge		$Q_{gs}$	-	7	-	
Gate-Drain ("Miller") Charge		$Q_{gd}$	-	23	-	
Turn-on delay time	$V_{DD}=400V$ $I_D=6A$ $R_G=25\Omega$ $V_{GS}=10V$	$t_{d(on)}$	-	21	-	ns
Rise Time		$T_r$	-	41	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	110	-	
Fall Time		$t_f$	-	48	-	
Input Capacitance	$V_{DS}=100V$ $V_{GS}=0V$ $f=1MHz$	$C_{iss}$	-	1130	1808	pF
Output Capacitance		$C_{oss}$	-	56	-	
Reverse Transfer Capacitance		$C_{rss}$	-	12	-	
Gate Resistance	$f=1MHz$	$R_G$	-	2.8	5.6	$\Omega$
Forward voltage <sup>2</sup>	$V_{GS}=0V, I_S=6A$	$V_{SD}$	-	-	1.5	V
Reverse Recovery Time	$I_S=7A, V_{GS}=0V$ $di_{SD}/dt=100A/\mu s,$	$t_{rr}$	-	500	-	ns
Reverse Recovery Charge		$Q_{rr}$	-	3.3	-	nC

**Notes:**

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test
- 3.Ensure that the junction temperature does not exceed Tjmax..
- 4.Starting Tj=25oC , VDD=90V , L=1mH , RG=25 $\Omega$  , VGS=10V

Ratings and Characteristic Curves

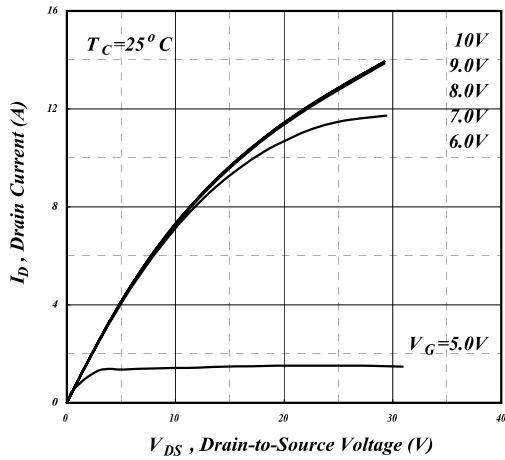


Fig 1. Typical Output Characteristics

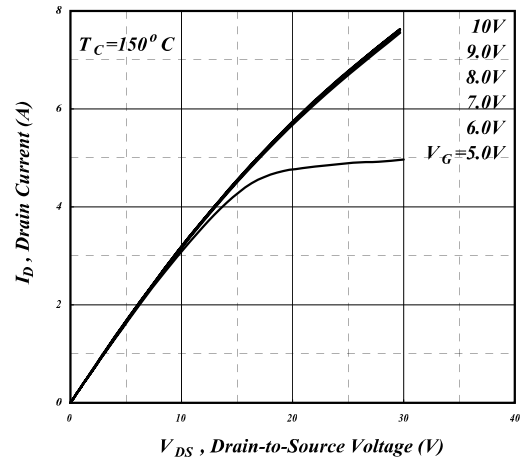


Fig 2. Typical Output Characteristics

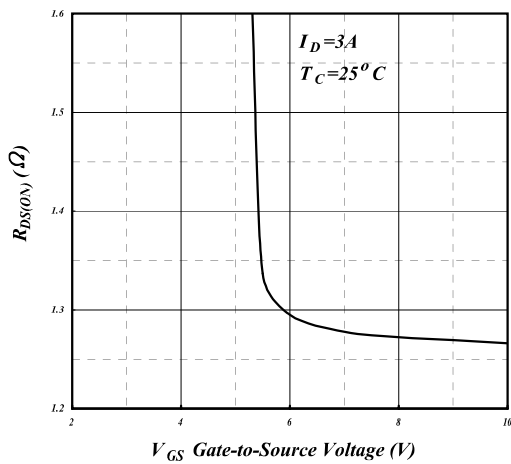


Fig 3. On-Resistance v.s. Gate Voltage

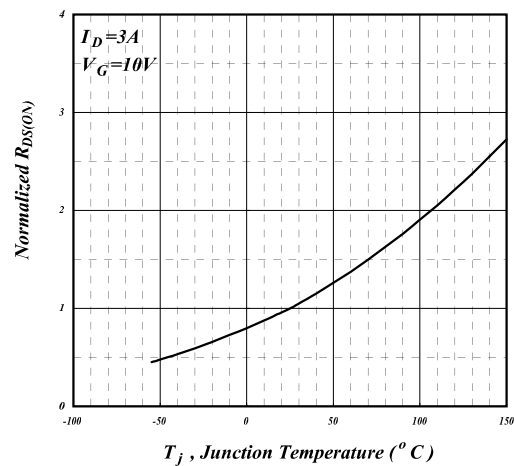


Fig 4. Normalized On-Resistance v.s. Junction Temperature

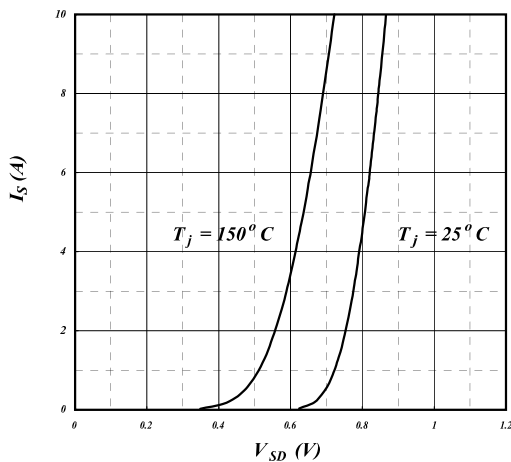


Fig 5. Forward Characteristic of Reverse Diode

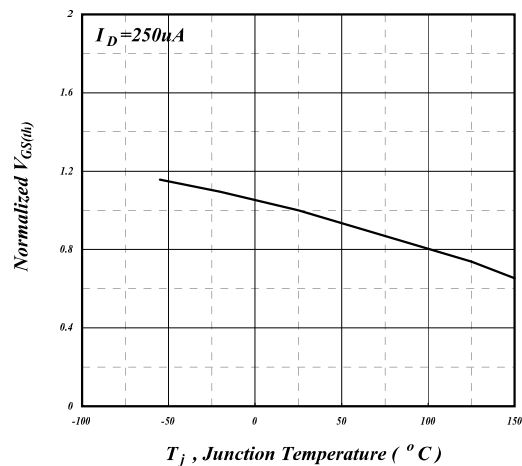


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Ratings and Characteristic Curves

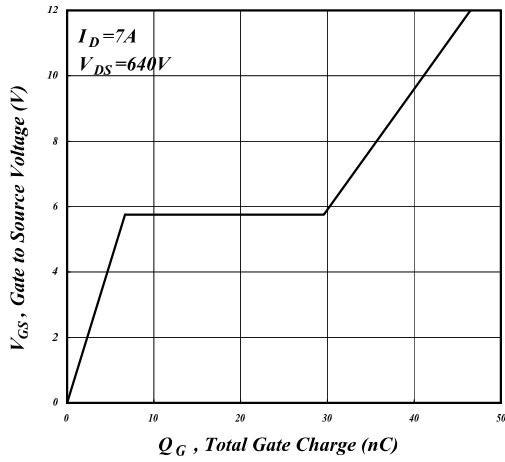


Fig 7. Gate Charge Characteristics

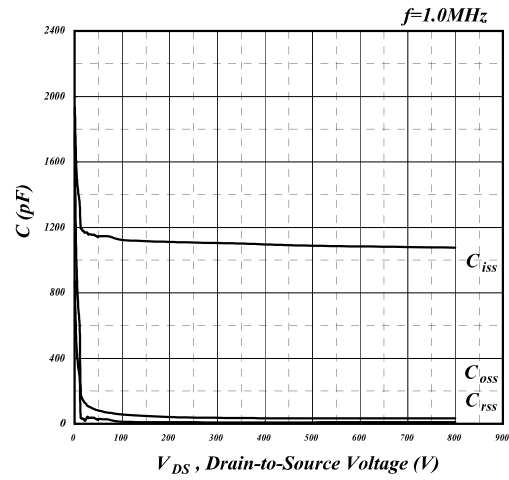


Fig 8. Typical Capacitance Characteristics

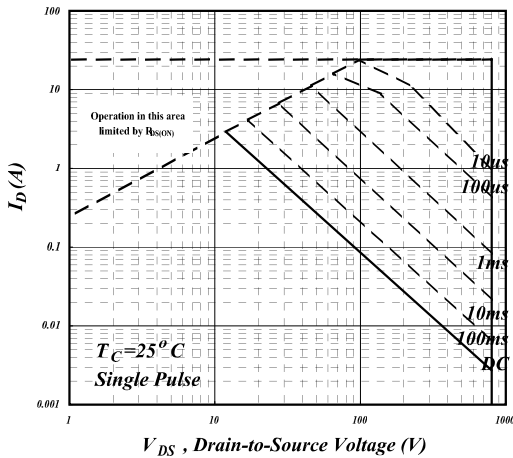


Fig 9. Maximum Safe Operating Area

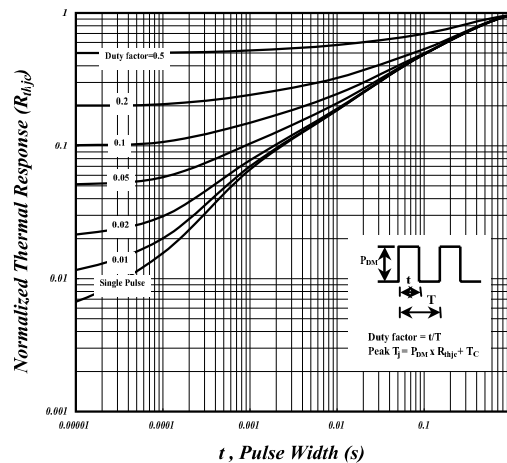


Fig 10. Effective Transient Thermal Impedance

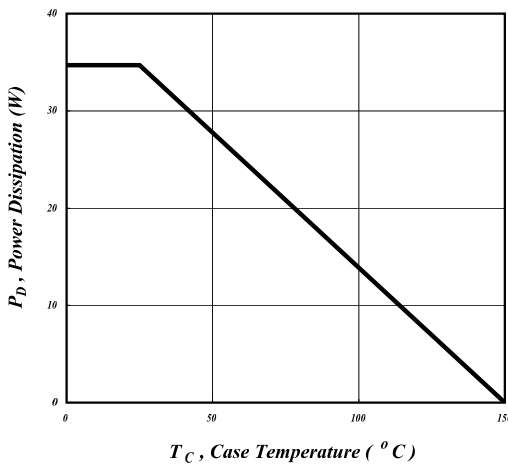


Fig 11. Total Power Dissipation

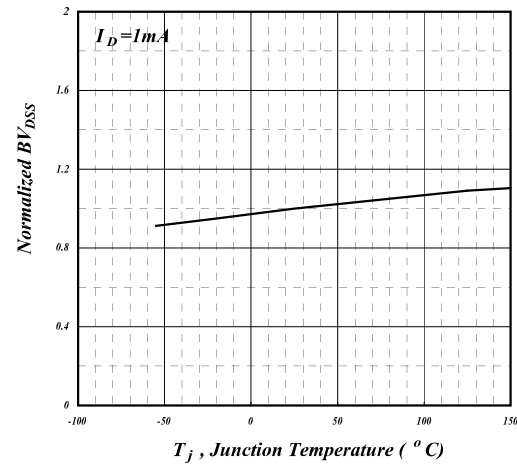


Fig 12. Normalized  $BV_{DS}$  v.s. Junction Temperature

Package Outline Dimensions Millimeters

TO-220AB

	Dim.	Min.	Max.
	A	10.15	10.35
	B	2.65	2.95
	C	3.70	3.90
	D	28.5	29.5
	E	1.30	1.45
	F	6.35	6.55
	G	2.9	3.3
	H	15.0	16.0
	I	0.38	0.42
	J	4.45	4.55
	K	1.25	1.35
	L	Typ 5.08	
	M	Typ 2.54	
N	3.1	3.3	
O	0.76	0.84	
All Dimensions in millimeter			

TO-220F

	Dim.	Min.	Max.
	A	9.95	10.25
	B	2.95	3.25
	C	1.25	1.45
	D	12.95	13.25
	E	0.50	0.65
	F	3.1	3.3
	G	1.30	1.45
	H	Typ 2.54	
	I	Typ 5.08	
	J	4.60	4.75
	K	2.50	2.65
	L	6.35	6.55
	M	15.4	16.0
	N	2.75	3.05
	O	0.48	0.52
P	0.76	0.84	
All Dimensions in millimeter			

Package Outline Dimensions Millimeters

TO-263

Dim.	Min.	Max.
A	10.1	10.2
B	7.4	7.6
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.78	0.86
H	1.2	1.3
I	Typ2.54	
J	8.4	8.6
K	4.45	4.55
L	1.25	1.35
M	0.02	0.1
N	2.4	2.8
O	0.36	0.40
All Dimensions in millimeter		